

ESJC01 (9kV, 12kV)

ESJC01 供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

: Outline Drawings

HIGH VOLTAGE SILICON DIODE

ESJC01 is high reliability and high current capability type resin molded high voltage silicon diode which is sealed a multilayered mesa type silicon chip by epoxy resin.

■ : Features

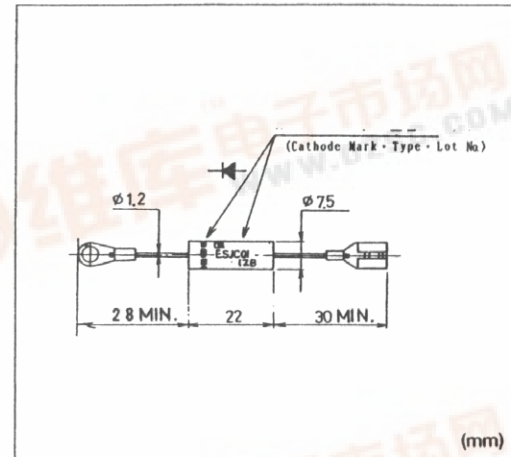
- Small size
- High current capability
- High reliability
- Attached fasten terminal

■ : Applications

Rectification for high voltage power supply of magnetron in micro wave oven range.

Rectification for high voltage power supply of X-ray generator.

Others.



: Cathode Mark

Type	Mark
ESJC01-09B	~
ESJC01-12B	⋮

: Maximum Ratings and Characteristics

: Absolute Maximum Ratings

Items	Symbols	ESJC01		Units	Conditions
		-09B	-12B		
Repetitive Peak Reverse Voltage	V_{RRM}	9	12	kV	
Average Forward Current	$I_{F(AV)}$	350		mA	$T_a = 60^\circ\text{C}$, Resistive Load (RL)
Surge Current	I_{FSM}	30		Ap	60Hz, One shot surge of 60Hz half sine wave.
Reverse Surge Current	I_{RSM}	100		mAp	$W_p = 1\text{msec}$, $T_a = 25^\circ\text{C}$ One shot surge of W_p 1ms triangular wave
Allowable Junction Temperature	T_j	130		$^\circ\text{C}$	
Storage Temperature	T_{stg}	$-40 \sim 130$		$^\circ\text{C}$	

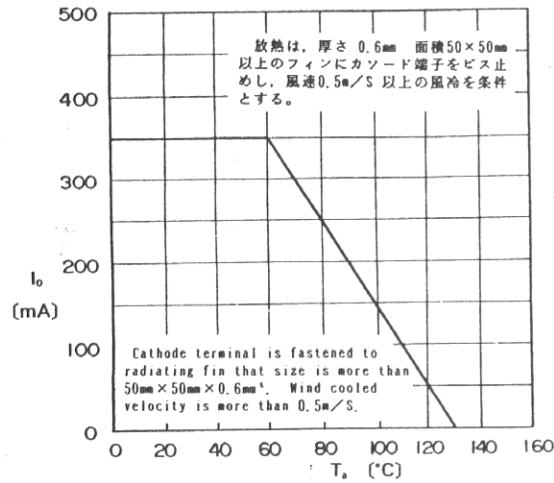
: Electrical Characteristics

Items	Symbols	ESJC01		Units	Conditions
		-09B	-12B		
Forward Voltage Drop	V_F	10	12	V	$T_j = 25^\circ\text{C}$, $I_F = 350\text{mA}$
Reverse Current	I_R	5		μA	$T_j = 25^\circ\text{C}$, $V_R = V_{RRM}$
	V_R	9.5 ~ 15	12.5 ~ 18	kV	$T_j = 25^\circ\text{C}$, $I_F = 100\mu\text{A}$

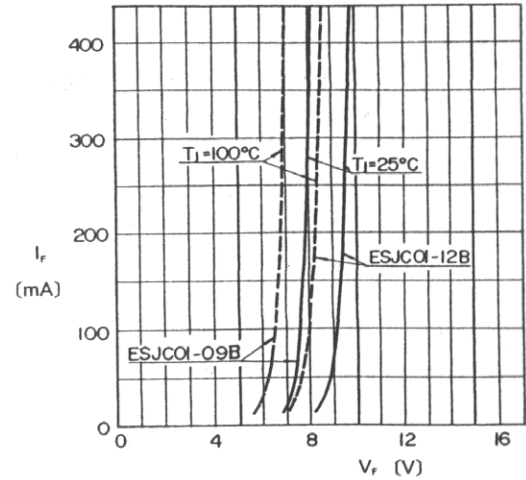


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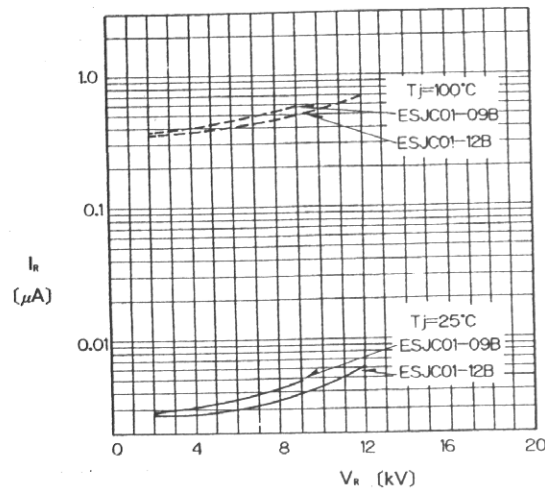
: Characteristics



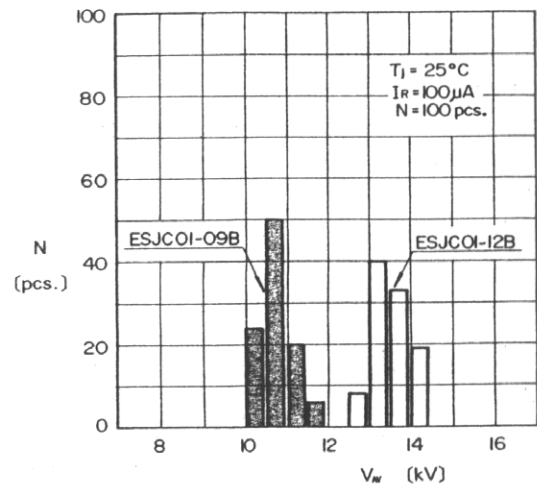
Current Derating Curve



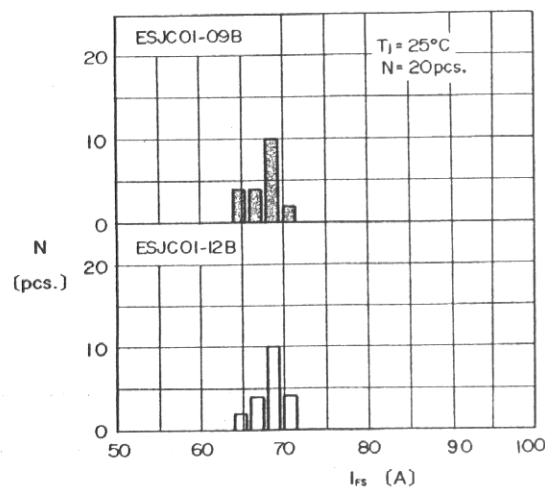
Forward Characteristics



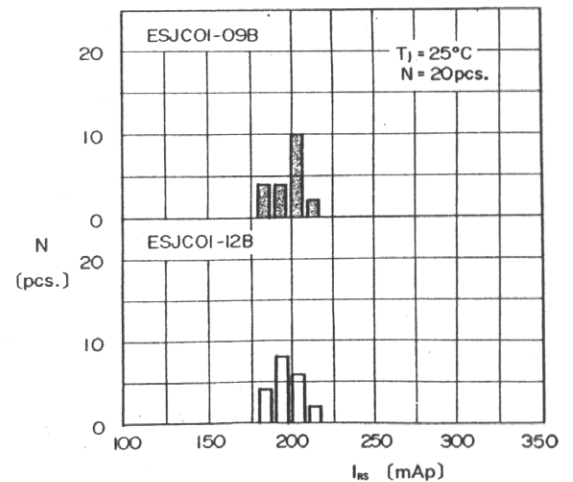
Reverse Characteristics



Avalanche Breakdown Voltage



Forward Surge Current



Reverse Surge Current